

Ordering number:EN4495



FP202

PNP/NPN Epitaxial Planar Silicon Transistor

Push-Pull Circuit Applications

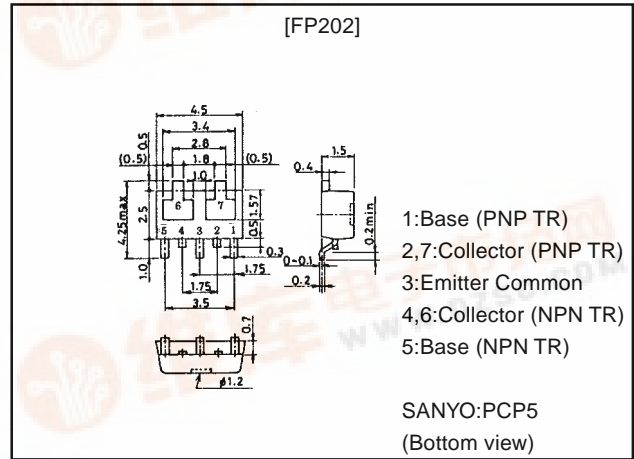
Features

- Composite type with 2 transistors (PNP and NPN) contained in one package facilitating high-density mounting.
- The FP202 is formed with a chip being equivalent to the 2SA1338 and a chip being equivalent to the 2SC3392, placed in one package.

Package Dimensions

unit:mm

2097A



Specifications

Absolute Maximum Ratings at Ta = 25°C

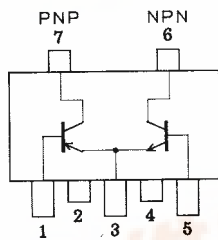
Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V_{CBO}		(-)60	V
Collector-to-Emitter Voltage	V_{CEO}		(-)50	V
Emitter-to-Base Voltage	V_{EBO}		(-)5	V
Collector Current	I_C		(-)500	mA
Collector Current (Pulse)	I_{CP}		(-)800	mA
Base Current	I_B		(-)0.1	A
Collector Dissipation	P_C	Mounted on ceramic board (250mm ² ×0.8mm) 1unit	0.75	W
Total Dissipation	P_T	Mounted on ceramic board (250mm ² ×0.8mm)	1.0	W
Junction Temperature	T_J		150	°C
Storage Temperature	T_{stg}		-55 to +150	°C

() : NPN

Marking:202

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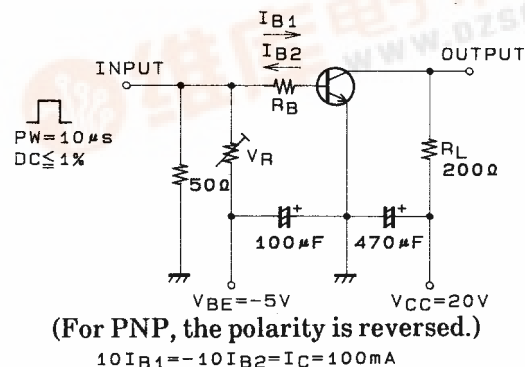
Electrical Connection



- 1:Base (PNP TR)
- 2,7:Collector (PNP TR)
- 3:Emitter Common
- 4,7:Collector (NPN TR)
- 5:Base (NPN TR)

(Top view)

Switching Time Test Circuit

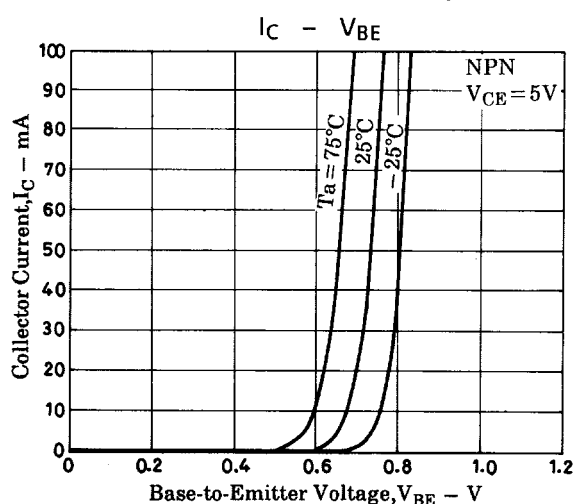
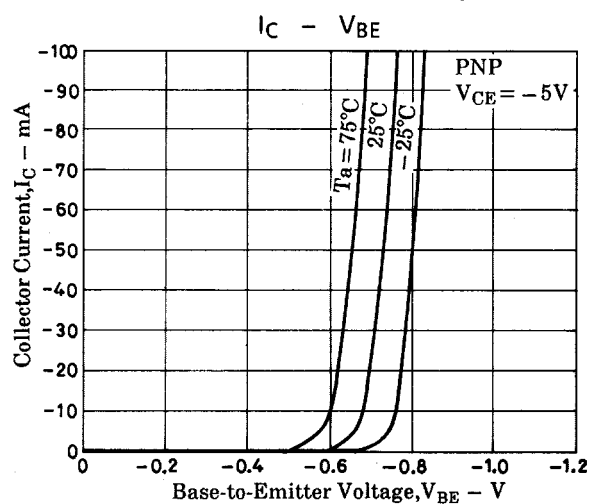
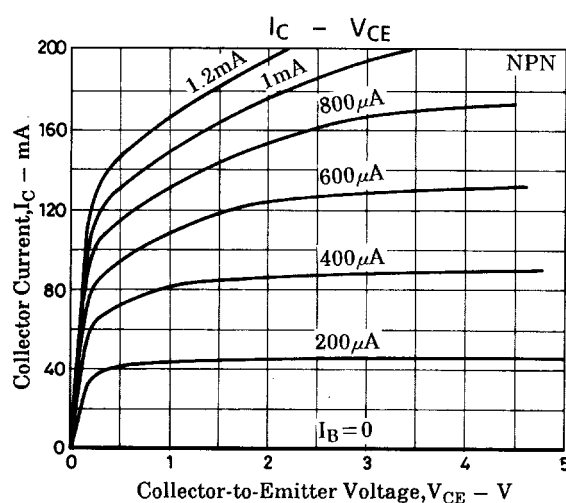
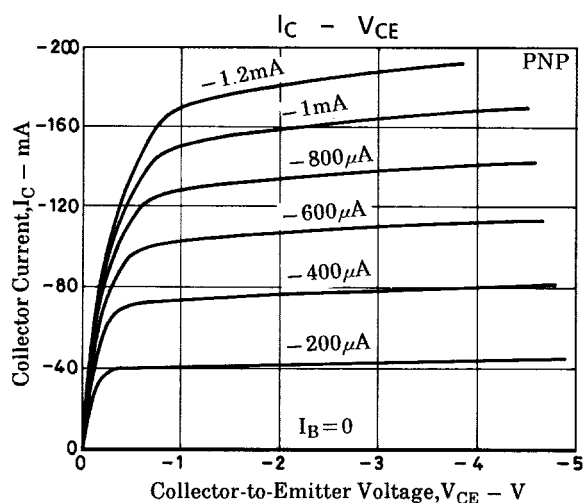


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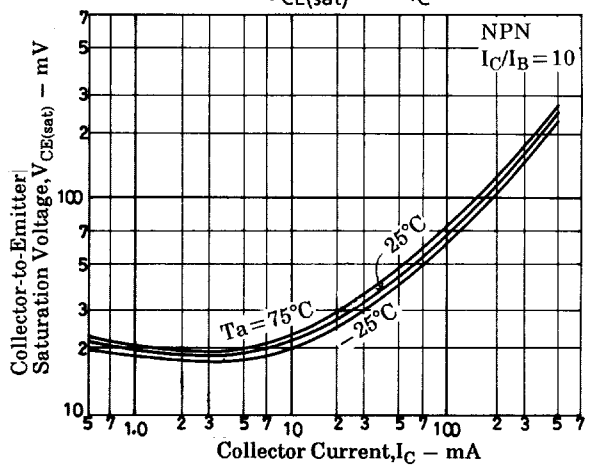
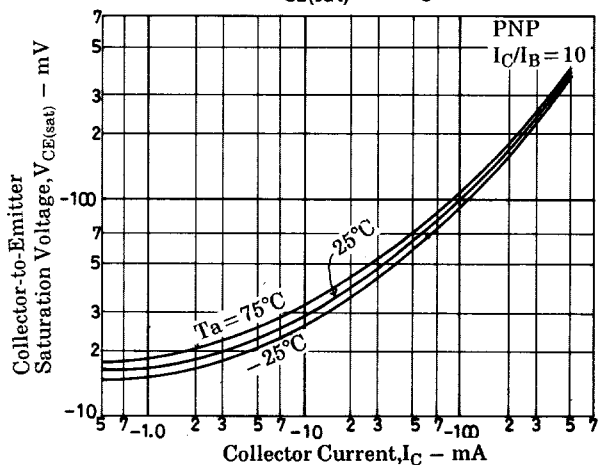
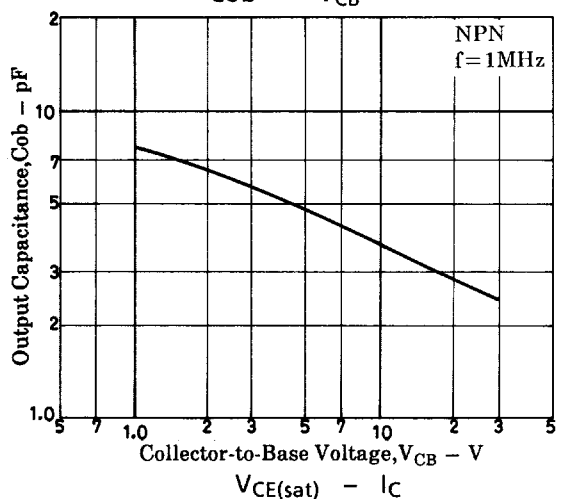
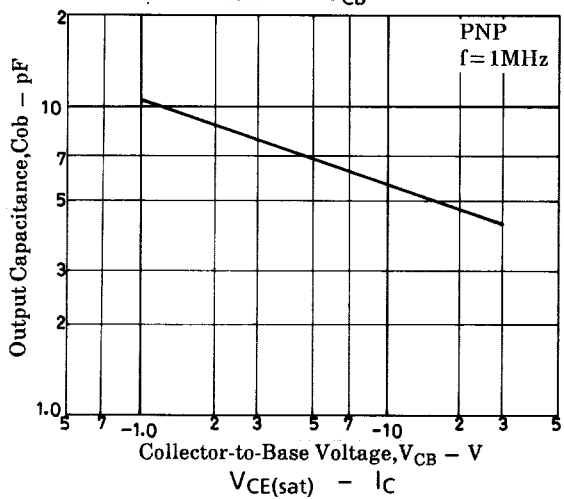
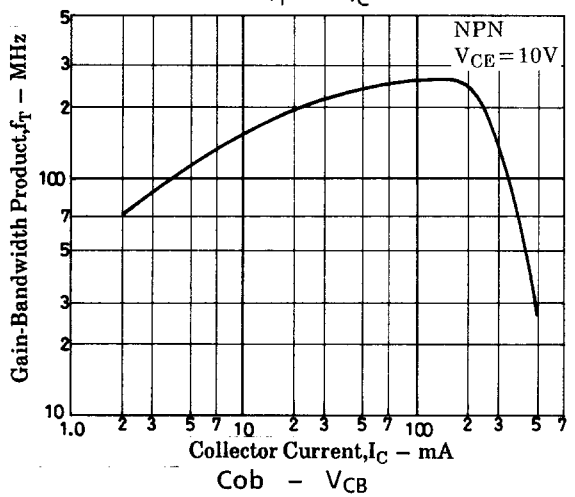
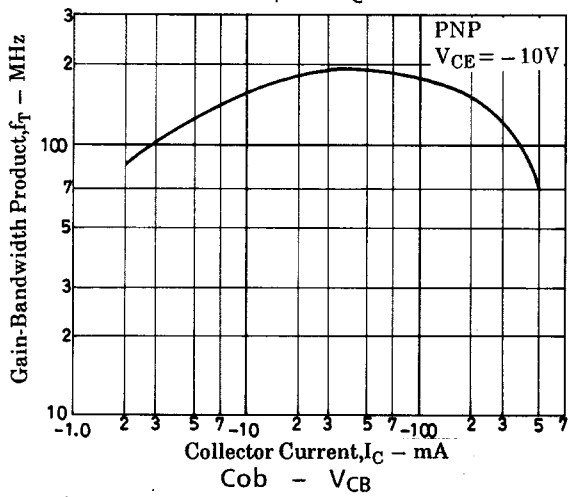
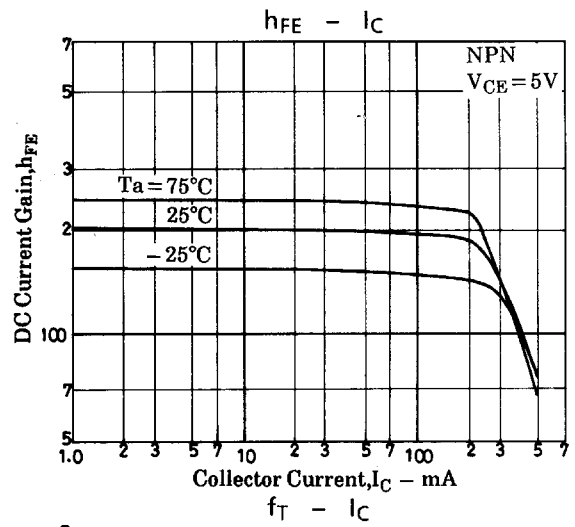
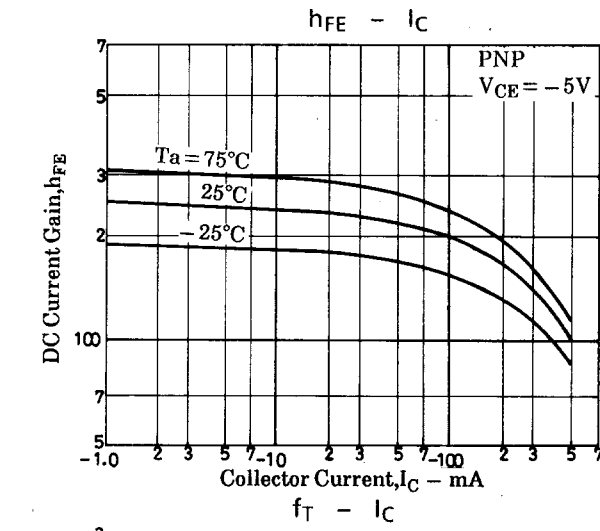
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Electrical Characteristics at $T_a=25^\circ\text{C}$

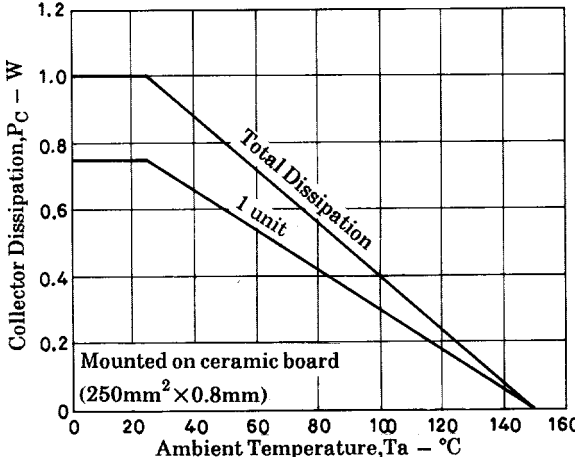
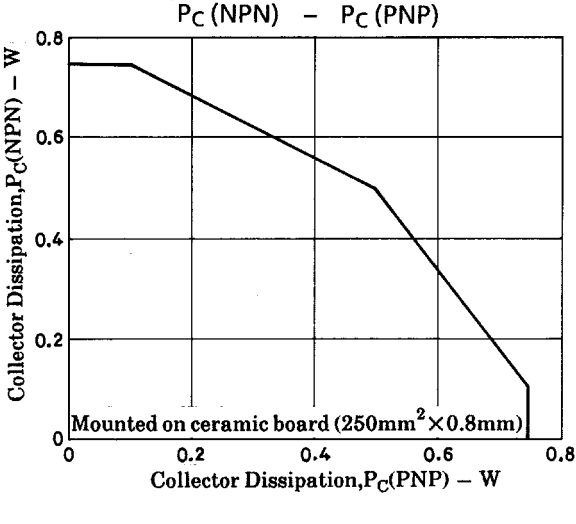
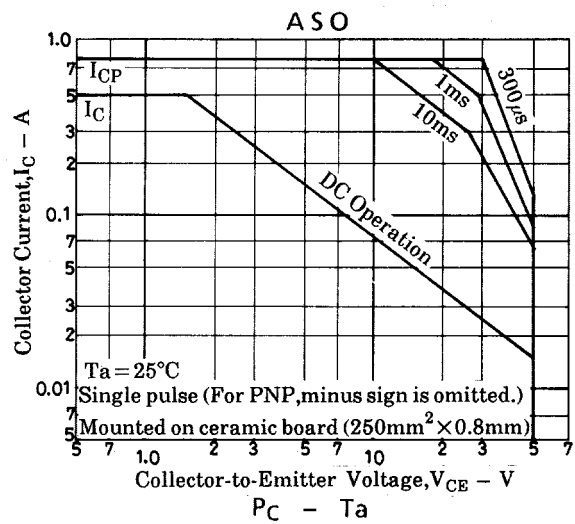
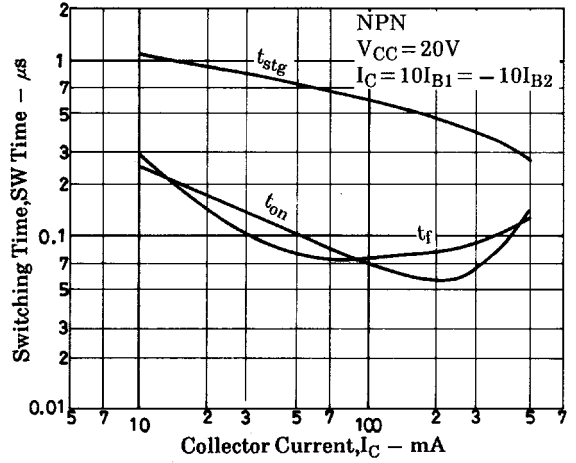
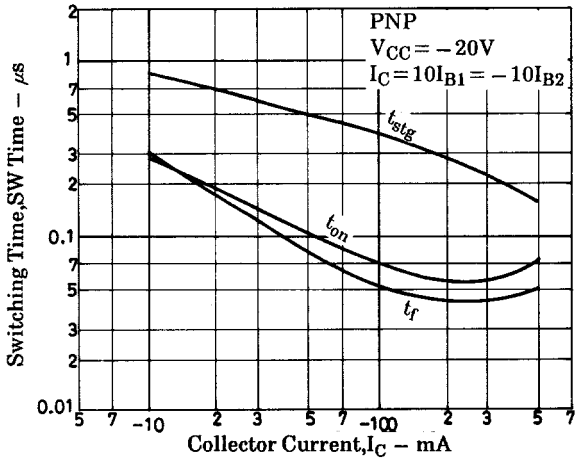
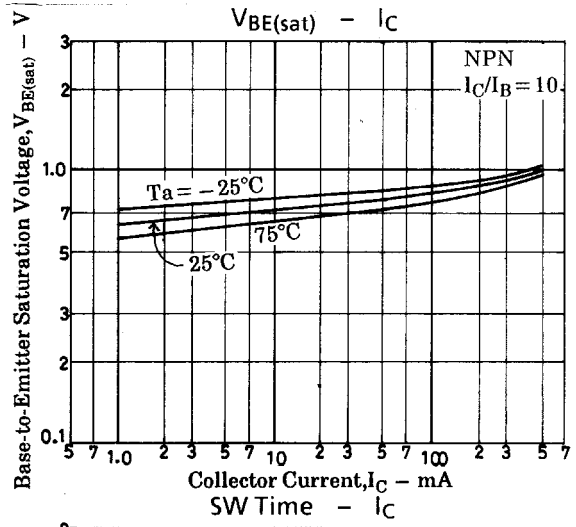
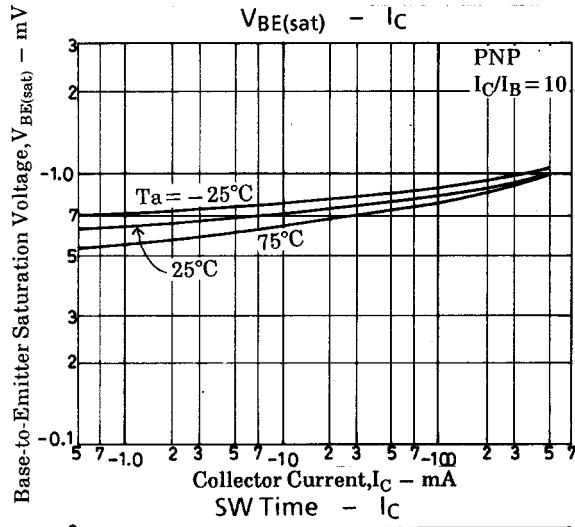
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}, I_E=0$			(-100)	nA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)4\text{V}, I_C=0$			(-100)	nA
DC Current Gain	h_{FE}	$V_{CE}=(-)5\text{V}, I_C=(-)10\text{mA}$	140		400	
Gain-Bandwidth Product	f_T	$V_{CE}=(-)10\text{V}, I_C=(-)50\text{mA}$		(200)		MHz
				250		MHz
Output Capacitance	C_{ob}	$V_{CB}=(-)10\text{V}, f=1\text{MHz}$		(5.6)		pF
				3.7		pF
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)100\text{mA}, I_B=(-)10\text{mA}$		(-100)	(-300)	mV
				70	200	mV
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)100\text{mA}, I_B=(-)10\text{mA}$		(-0.8)	(-1.2)	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu\text{A}, I_E=0$	(-60)			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu\text{A}, R_{BE}=\infty$	(-50)			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E=(-)10\mu\text{A}, I_C=0$	(-5)			V
Turn-ON Time	t_{on}	See specified Test Circuit		(70)		ns
				70		ns
Storage Time	t_{stg}	See specified Test Circuit		(400)		ns
				600		ns
Fall Time	t_f	See specified Test Circuit		(50)		ns
				70		ns



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